

HAT2287WP

Silicon N Channel Power MOS FET Power Switching

REJ03G1470-0100

Rev.1.00

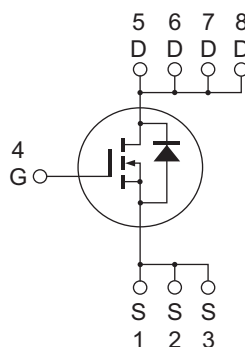
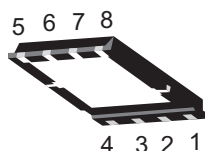
Sep 06, 2006

Features

- Low on-resistance
- Low drive current
- High density mounting

Outline

RENESAS Package code: PWSN0008DA-A
(Package name: WPAK)



1, 2, 3 Source
4 Gate
5, 6, 7, 8 Drain

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	200	V
Gate to source voltage	V_{GSS}	±30	V
Drain current	I_D	17	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	34	A
Body-drain diode reverse drain current	I_{DR}	17	A
Body-drain diode reverse drain peak current	$I_{DR(pulse)}$ ^{Note1}	34	A
Avalanche current	I_{AP} ^{Note3}	17	A
Avalanche energy	E_{AR} ^{Note3}	19.2	mJ
Channel dissipation	P_{ch} ^{Note2}	30	W
Channel to case thermal impedance	θ_{ch-c}	4.17	°C/W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

2. Value at $T_c = 25^\circ C$

3. $ST_{ch} = 25^\circ C$, $T_{ch} \leq 150^\circ C$

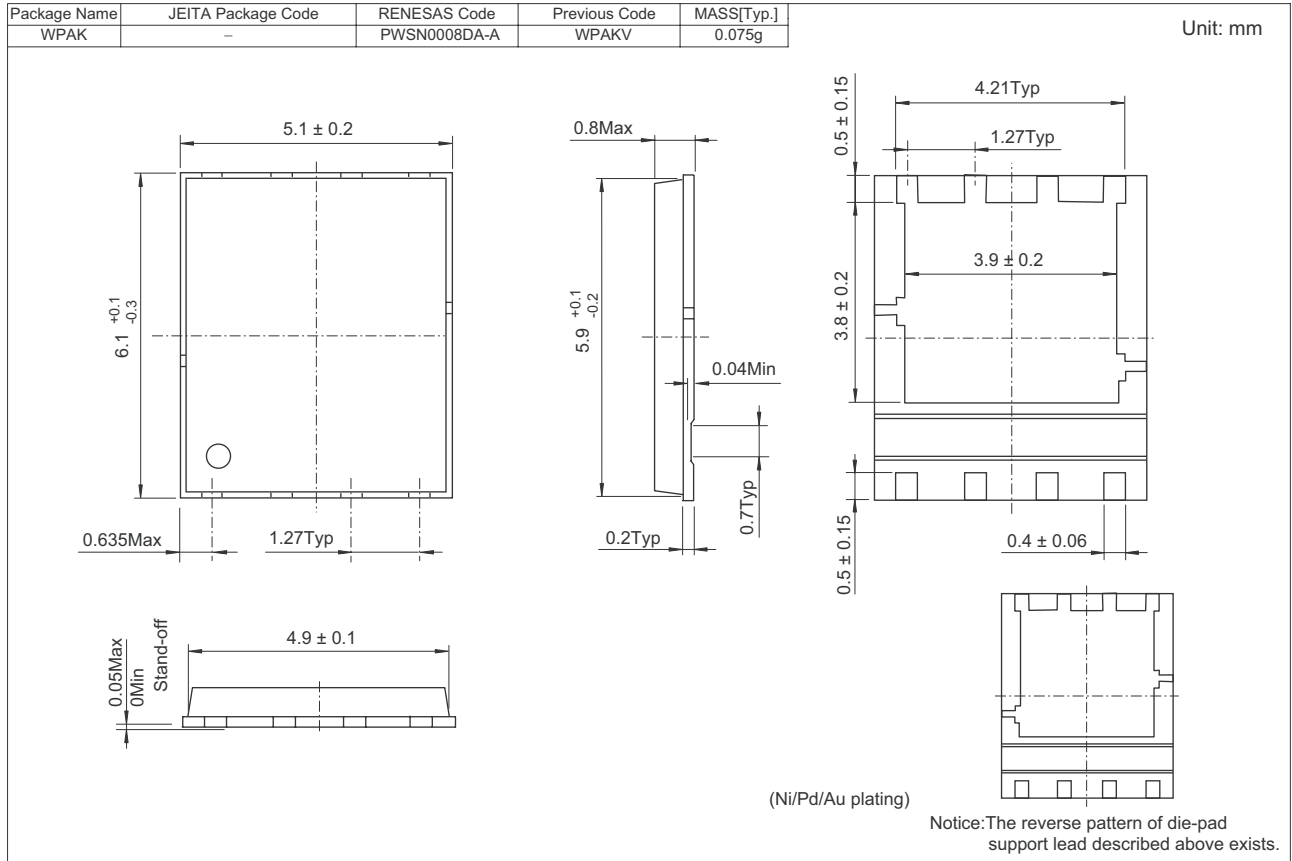
Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	200	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 200 \text{ V}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	—	4.0	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Forward transfer admittance	$ y_{fs} $	8	14	—	S	$I_D = 8.5 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note4}
Static drain to source on state resistance	$R_{DS(on)}$	—	0.084	0.094	Ω	$I_D = 8.5 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	1200	—	pF	$V_{DS} = 25 \text{ V}$
Output capacitance	C_{oss}	—	220	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	19	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	31	—	ns	$I_D = 8.5 \text{ A}$
Rise time	t_r	—	37	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	69	—	ns	$R_L = 11.8 \Omega$
Fall time	t_f	—	8	—	ns	$R_g = 10 \Omega$
Total gate charge	Q_g	—	26	—	nC	$V_{DD} = 160 \text{ V}$
Gate to source charge	Q_{gs}	—	7	—	nC	$V_{GS} = 10 \text{ V}$
Gate to drain charge	Q_{gd}	—	10	—	nC	$I_D = 17 \text{ A}$
Body-drain diode forward voltage	V_{DF}	—	0.9	1.4	V	$I_F = 17 \text{ A}$, $V_{GS} = 0$ ^{Note4}
Body-drain diode reverse recovery time	t_{rr}	—	130	—	ns	$I_F = 17 \text{ A}$, $V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT2287WP-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.

Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120
Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510